

Notice of References Cited	Application/Control No. 10/637,107	Applicant(s)/Patent Under Reexamination SANDHU ET AL.	
	Examiner Jeff Vockrodt	Art Unit 2822	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4,960,732	10-1990	Dixit et al.	438/628
	B	US-4,998,151	03-1991	Korman et al.	257/328
	C	US-5,242,860	09-1993	Nulman et al.	438/653
	D	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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	N	WO 86/01640	03-1986	WO	Dean et al.	
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NON-PATENT DOCUMENTS

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	U	Eizenberg et al., TiCN: A new chemical vapor deposited contact barrier metallization for submicron devices, Appl. Phys. Lett. 6 (19), 7 November 1994, pp. 2416-18
	V	Peng et al., Properties of CVD-W Overgrowth on PVD and MOCVD TiN Layers, IEEE, 5th International Conference Proceeding on Solid-State and Integrated Circuit Technology, 1998, pp. 211-214
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.